



THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yamazaki, et al. Art Unit : 2811  
Serial No.: 09/814,255 Examiner : Ori Nadav  
Filed : March 21, 2001  
Title : SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

BOX AF

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the final action mailed September 4, 2002,  
please amend the application as follows:

In the title:

Please amend the title:

--SEMICONDUCTOR DEVICE HAVING A RELIABLE CONTACT--

In the specification:

Please replace the paragraph beginning at page 5, lines 2-3  
with the following rewritten paragraph:

C' --To complete the contact hole 104, it is necessary to  
etch the interlayer insulating film 103 which may be a silicon  
oxide film, a silicon nitride film, a silicon oxynitride film,  
or the like, and then etch the anodic oxide film 102.--

do not  
enter  
on

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I hereby certify under 37 CFR §1.8(a) that this  
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